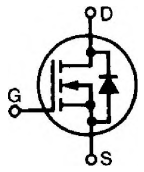
IXYS

IXFH 6N90 IXFM 6N90
IXFH 6N100 IXFM 6N100

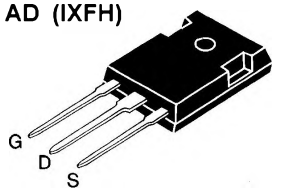
	V_{DSS}	I_{D25}	$R_{DS(on)}$	t_{rr}
IXFH/FM 6N90	900 V	6 A	1.8 Ω	250 ns
IXFH/FM 6N100	1000 V	6 A	2.0 Ω	250 ns

HiPerFET™ Power MOSFET

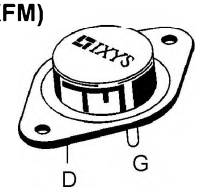
N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family



TO-247 AD (IXFH)



TO-204 AA (IXFM)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	T_J = 25°C to 150°C	6N90	900	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	6N100	1000	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C		6	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}		24	A
I_{AR}	T_C = 25°C		6	A
E_{AR}	T_C = 25°C		18	mJ
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		180	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s			300	°C

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
V_{DSS}	V_{GS} = 0 V, I_D = 3 mA	6N90	900			V
		6N100	1000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 2.5 mA		2.0		4.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±100	nA
I_{DSS}	V_{DS} = 0.8 V_{DSS}	T_J = 25°C			250	µA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25}	6N90			1.8	Ω
		6N100			2.0	Ω
	Pulse test, t ≤ 300 µs, duty cycle δ ≤ 2 %					

Features

- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

IXYS Corporation
3540 Bassett Street, Santa Clara, CA 95054
Tel: 408-982-0700 Fax: 408-496-0670

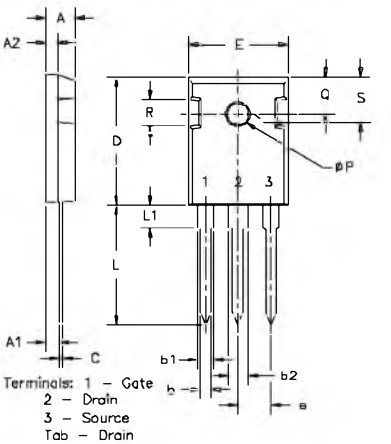
IXYS Semiconductor
Edisonstr. 15, D-68623 Lampertheim, Germany
Tel: +49-6206-5030 Fax: +49-6206-503629

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test	4	6		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2600		pF
C_{oss}			180		pF
C_{rss}			45		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25} R_G = 4.7 Ω (External)		35	100	ns
t_r			40	110	ns
$t_{d(off)}$			100	200	ns
t_f			60	100	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		88	130	nC
Q_{gs}			21	30	nC
Q_{gd}			38	70	nC
R_{thJC}				0.7	K/W
R_{thCK}			0.25		K/W

Source-Drain Diode

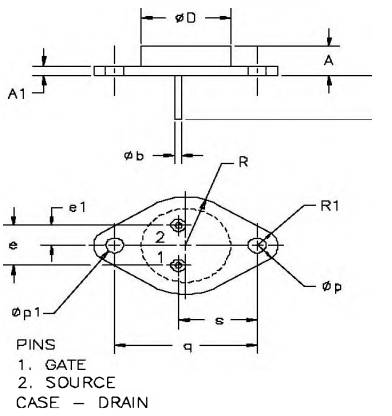
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
I_S	V_{GS} = 0			6	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			24	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle δ ≤ 2 %			1.5	V
t_{rr}	I_F = I_S, -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C		250	ns
		T_J = 125°C		400	ns
Q_{RM}		T_J = 25°C	0.5		µC
		T_J = 125°C	1.0		µC
I_{RM}		T_J = 25°C	7.5		A
		T_J = 125°C	9.0		A

TO-247 AD (IXFH) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.7	5.3
A_1	.087	.102	2.2	2.54
A_2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b_1	.065	.084	1.65	2.13
b_2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

TO-204 AA (IXFM) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.250	.450	6.4	11.4
A1		.135		3.42
øb	.038	.043	.97	1.09
øD		.875		22.22
e	.420	.440	10.67	11.17
e1	.205	.225	5.21	5.71
L	.312		7.93	
øp	.151	.165	3.84	4.19
øp1	.151	.165	3.84	4.19
q	1.187 BSC		30.15 BSC	
R		.525		13.33
R1		.188		4.77
s	.655	.675	16.64	17.14

Fig.1. Output Characteristics

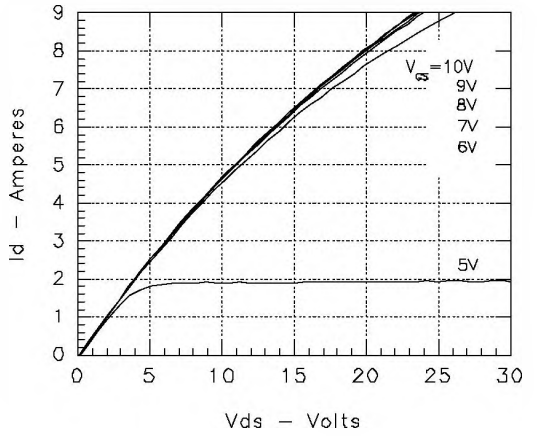


Fig. 2. Input Admittance

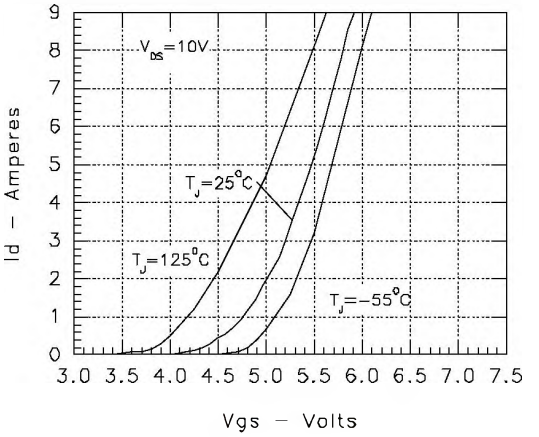


Fig. 3. Rds(on) vs. Drain Current

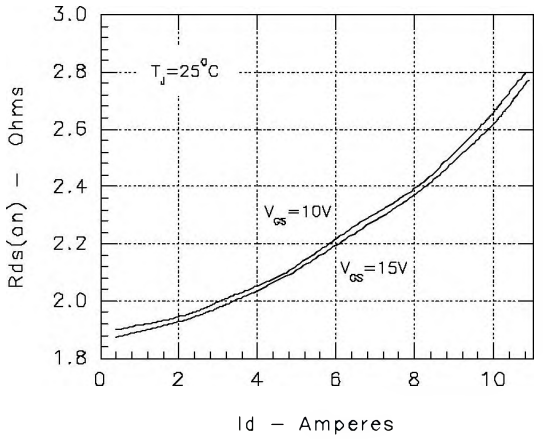


Fig. 4. Temperature Dependence of Drain to Source Resistance

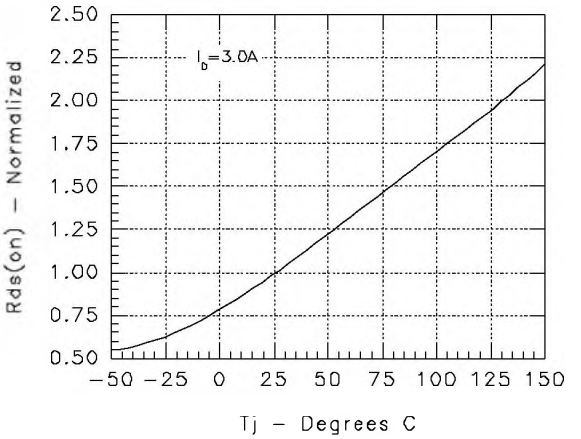


Fig. 5. Drain Current vs. Case Temperature

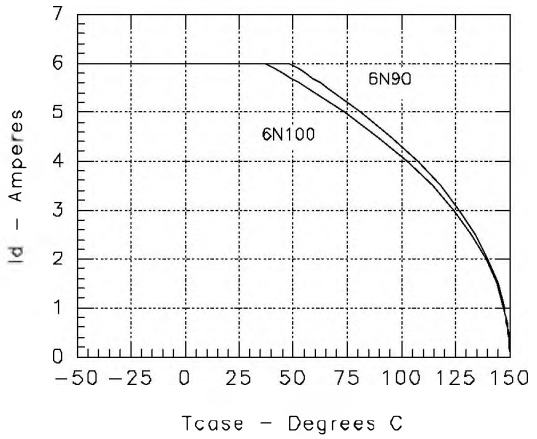
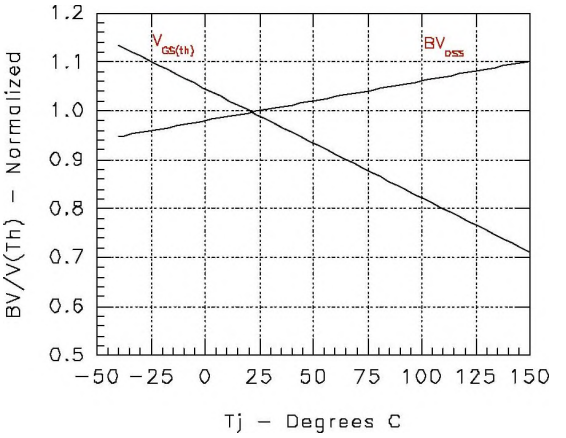


Fig. 6. Temperature Dependence of Breakdown Voltage and Threshold Voltage



IXYS Corporation
3540 Bassett Street, Santa Clara, CA 95054
Tel: 408-982-0700 Fax: 408-496-0670

IXYS Semiconductor
Edisonstr. 15, D-68623 Lampertheim, Germany
Tel: +49-6206-5030 Fax: +49-6206-503629

Fig. 7. Gate Charge

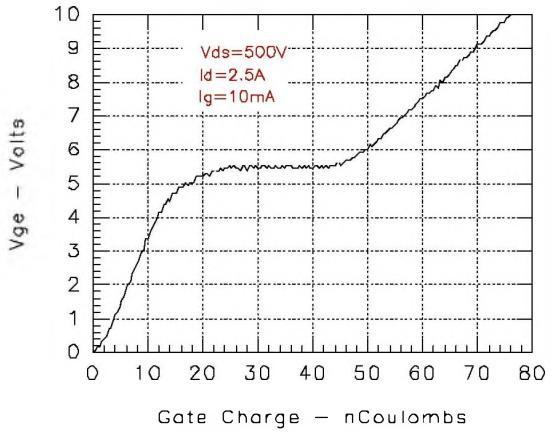


Fig. 8. Forward Bias Safe Operating Area

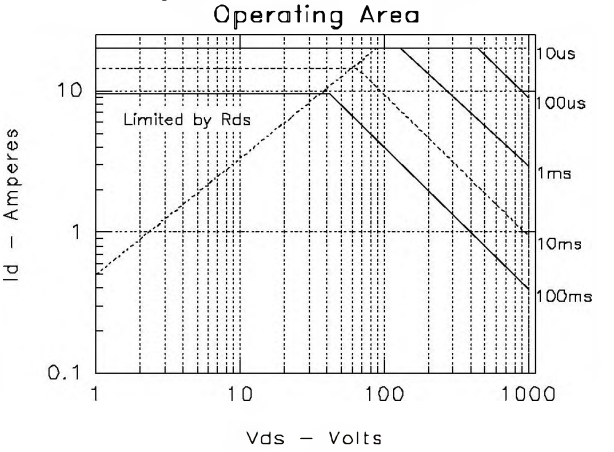


Fig. 9. Capacitance Curves

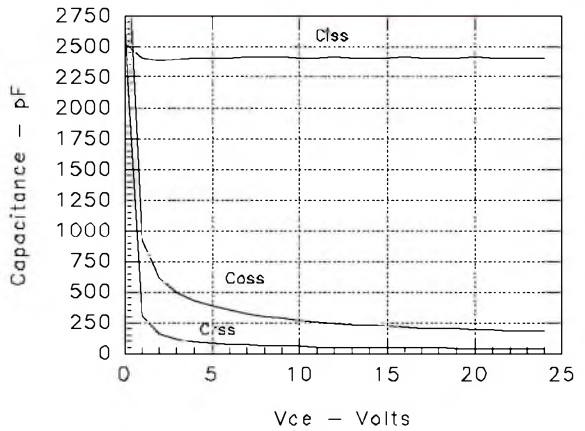


Fig. 10. Source Current vs. Source to Drain Voltage

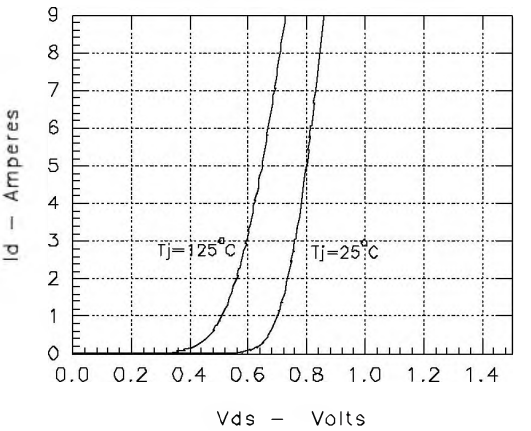


Fig. 11. Transient Thermal Impedance